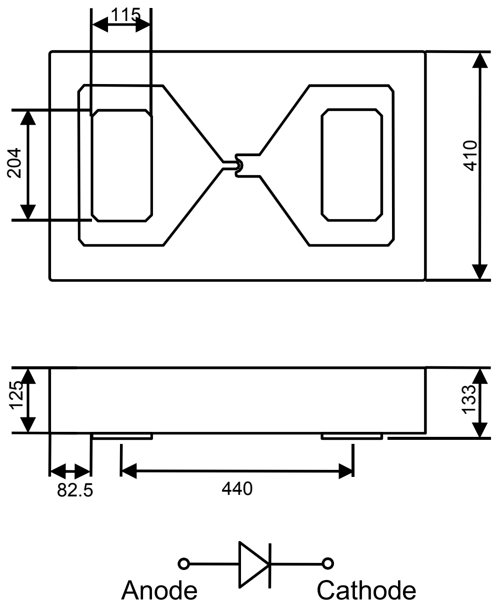
SIGETRONICS **SBD100**

Schottky Barrier Diode (GaAs)

Features

- Single Junction
- High Cut-off frequency
- Low Series Resistance
- Low Capacitance
- Designed for Easy Circuit Insertion
- Silicon Nitride Passivation

Dimensions



Application

- Single and Balanced Mixer and Detectors
- X, K and Ka Bands Transceiver
- 30 GHx and 60 GHz Radios
- Automotive Rader Detectors

Absolute Maximum Rating (Ta = 25℃)

Parameter	Symbol	Value	Unit
Forward Current	I_F	15	mA
Reverse Voltage	V_R	3	V
Incident Power	-	20	dBm
Operation Temperature	T_{OPR}	-55 to +125	˚C
Storage Temperature	T_{STG}	-55 to +150	˚C
Insertion Temperature	-	250 ± 5	˚C

Electrical Characteristics (Ta = 25℃)

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 1 mA	600	-	850	mV
Reverse Current	I_R	V_R = 3 V	-	-	10	μA
Capacitance	C_J	V = 0 V	-	45	65	fF
Series Resistance	R_S	10 mA	-	7	9	Ω
Breakdown Voltabe	BV	10 μA	7	-	-	V